

# NPN SILICON RF POWER TRANSISTOR

## DESCRIPTION:

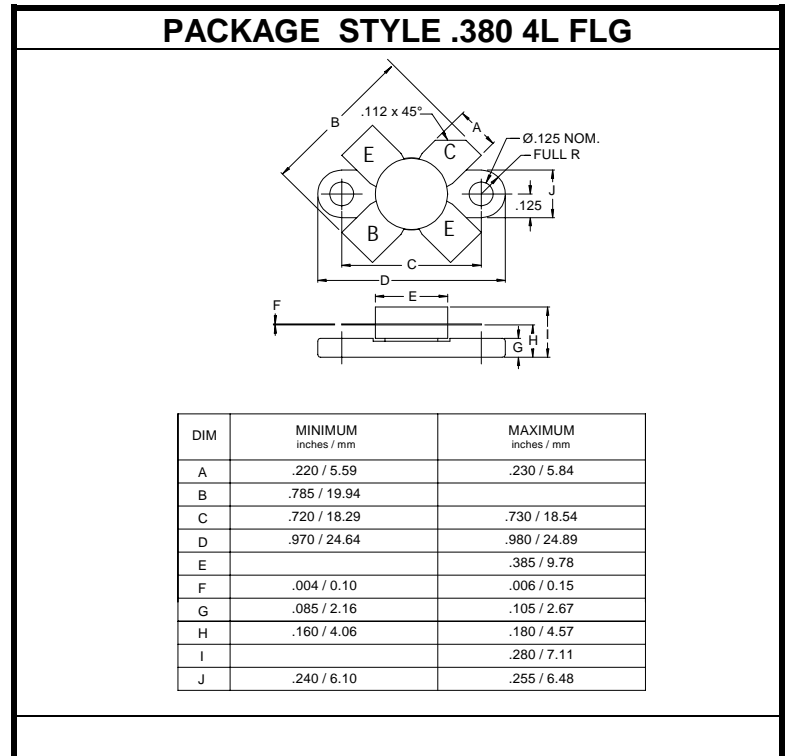
The **ASI BLW76** is Designed for use in class-AB or class-B operated high power transmitters in the H.F. and V.H.F bands and, as a Linear amplifier in the H.F. band.

## FEATURES:

- $P_G = 18$  dB min. at 75 W/30 MHz
- $IMD_3 = -30$  dBc max. at 75 W (PEP)
- **Omnigold™** Metalization System

## MAXIMUM RATINGS

$I_C$	10 A
$V_{CB}$	60 V
$V_{CE}$	35 V
$P_{DISS}$	140 W @ $T_C = 25^\circ C$
$T_J$	$-65^\circ C$ to $+200^\circ C$
$T_{STG}$	$-65^\circ C$ to $+150^\circ C$
$\theta_{JC}$	1.05 $^\circ C/W$



## CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 50$ mA	35			V
$BV_{CER}$	$I_C = 50$ mA $R_{BE} = 10 \Omega$	60			V
$BV_{EBO}$	$I_E = 10$ mA	4.0			V
$I_{CES}$	$V_E = 28$ V			5.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 1.0$ A	10		100	---
$C_{ob}$	$V_{CB} = 28$ V $f = 1.0$ MHz			80	pF
$G_{PE}$	$V_{CE} = 25$ V $I_{CQ} = 3.2$ A $f = 225$ MHz	13.5	14.5		dB
$IMD_3$	$P_{REF} = 16$ W $Vision = -8$ dB $Snd. = -7$ dB $Side Band = -16$ dB			-55	dBc